

**BT-5/D-21**  
**VLSI TECHNOLOGY**  
**Paper–ECP-5A**

**45255**

Time Allowed : 3 Hours]

[Maximum Marks : 75

**Note :** Attempt **five** questions in all, selecting at least **one** question from each Unit. All questions carry equal marks.

**UNIT-I**

1. Which method used for preparation of silicon explain in detail? 15
2. What is oxidation & describe theory of growth of silicon dioxide layer? 15

**UNIT-II**

3. Diffusion model of solid & ficks theory of diffusion? 15
4. Describe epitaxy & its concept & apparatus for epitaxial layer? 15

**UNIT-III**

5. Explain electron beam lithograpgy & differentiate between proximity & projection printing? 15
6. What is etching & describe reactive ion etching & its damages? 15

**UNIT-IV**

7. Explain C-MOS fabrication steps for IC technology? 15
8. What is package? Describe its types & utilities? 15

